

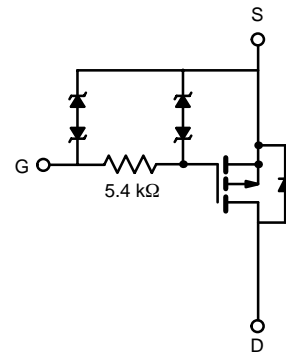
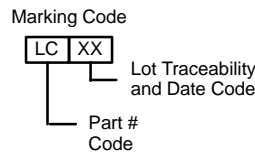
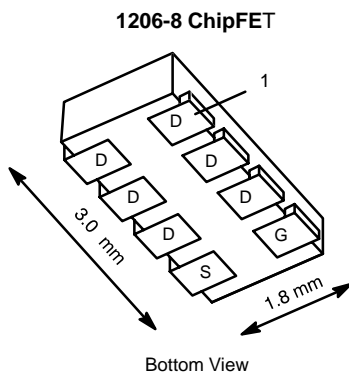


New Product

Si5465EDC  
Vishay Siliconix

## P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-12	0.037 @ $V_{GS} = -4.5$ V	-7.0
	0.048 @ $V_{GS} = -2.5$ V	-6.1
	0.065 @ $V_{GS} = -1.8$ V	-5.2



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter	Symbol	5 secs	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	-12		V
Gate-Source Voltage	$V_{GS}$	$\pm 12$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$T_A = 25^\circ\text{C}$	-7.0	-5.0	A
	$T_A = 85^\circ\text{C}$	-5.0	-3.6	
Pulsed Drain Current	$I_{DM}$	-20		
Continuous Source Current <sup>a</sup>	$I_S$	-2.1	-1.1	
Maximum Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	2.5	1.3	W
	$T_A = 85^\circ\text{C}$	1.3	0.7	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 5$ sec	40	$^\circ\text{C/W}$
		Steady State	80	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	15	20	

Notes

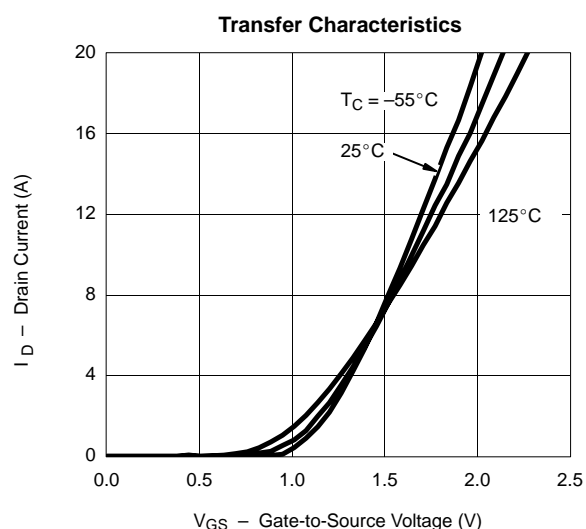
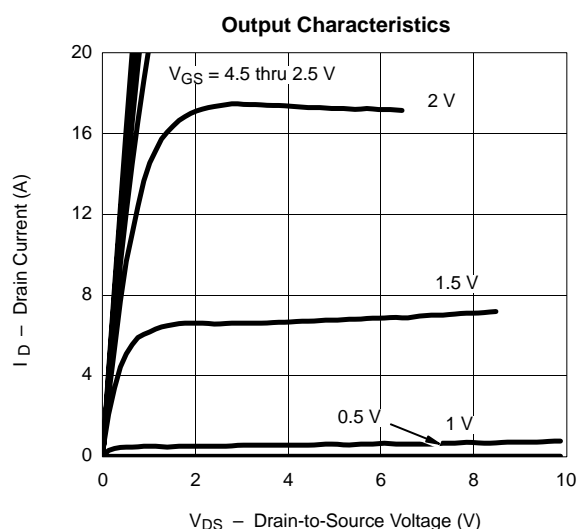
- a. Surface Mounted on 1" x 1" FR4 Board.
- b. When using HBM. The MM rating is 300 V.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -1 mA	-0.45			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±4.5 V			±1.5	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -9.6 V, V <sub>GS</sub> = 0 V			-1	
		V <sub>DS</sub> = -9.6 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			-5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5 V, V <sub>GS</sub> = -4.5 V	-20			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -5.0 A		0.030	0.037	Ω
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -4.5 A		0.040	0.048	
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -2 A		0.052	0.065	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -5 V, I <sub>D</sub> = -5.0 A		15		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = -1.1 A, V <sub>GS</sub> = 0 V		-0.8	-1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -6 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -5.0 A		13.5	20	nC
Gate-Source Charge	Q <sub>gs</sub>			2.8		
Gate-Drain Charge	Q <sub>gd</sub>			4.5		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -6 V, R <sub>L</sub> = 6 Ω I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -4.5 V, R <sub>G</sub> = 6 Ω		2.5	3.5	μS
Rise Time	t <sub>r</sub>			5.7	8.0	
Turn-Off Delay Time	t <sub>d(off)</sub>			30	40	
Fall Time	t <sub>f</sub>			21.5	30	

## Notes

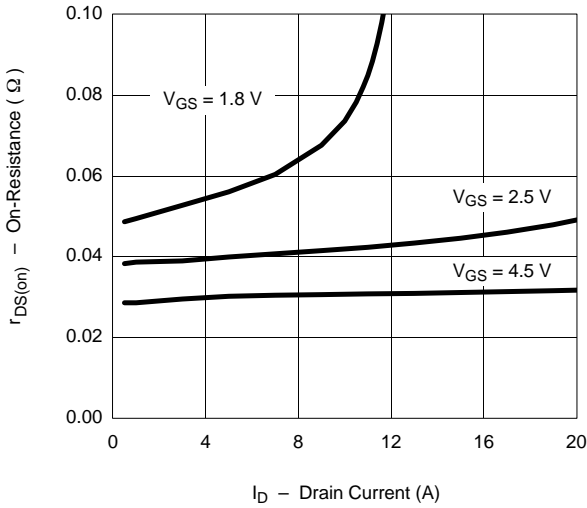
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

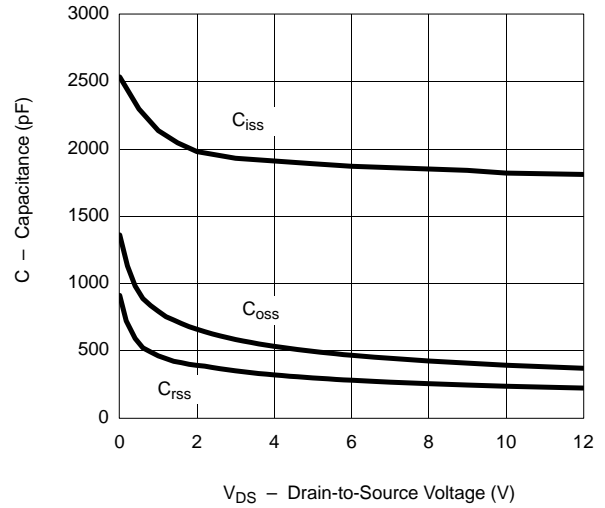


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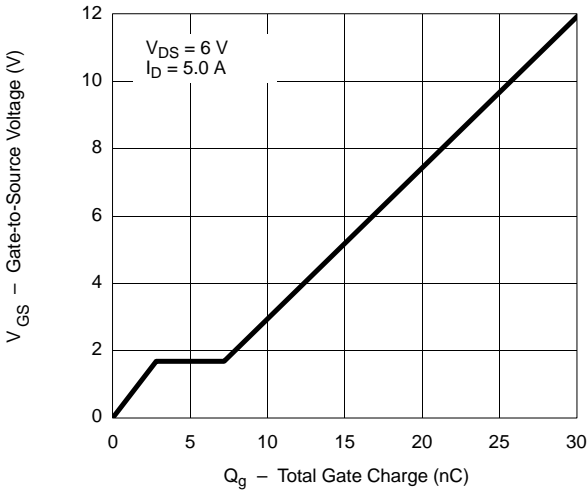
On-Resistance vs. Drain Current



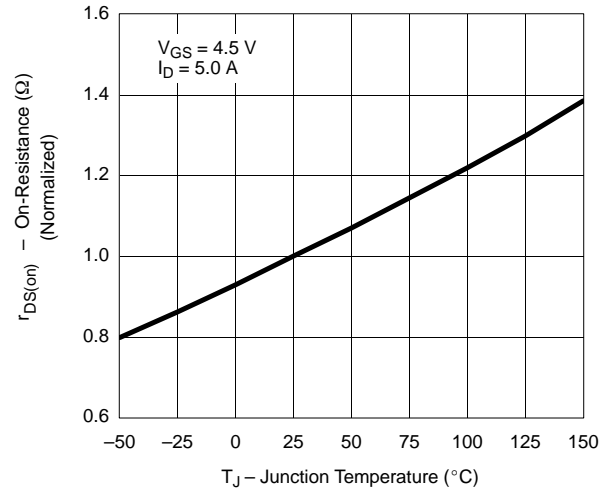
Capacitance



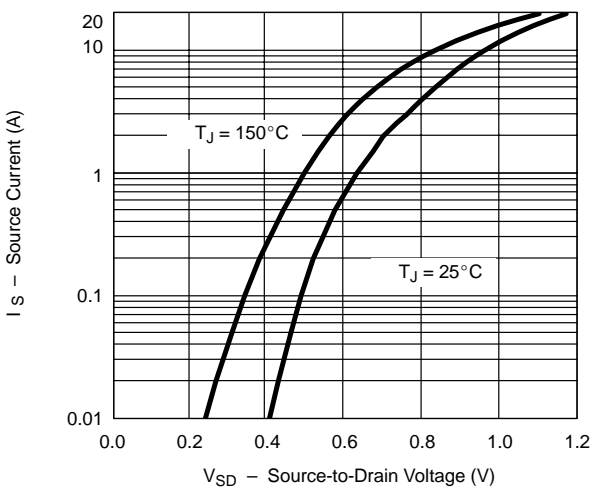
Gate Charge



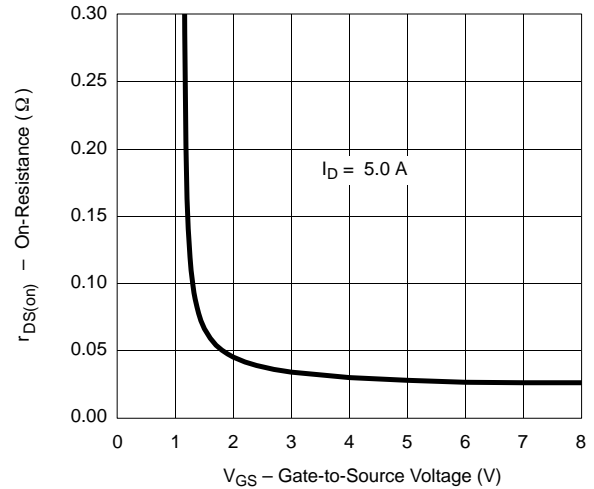
On-Resistance vs. Junction Temperature



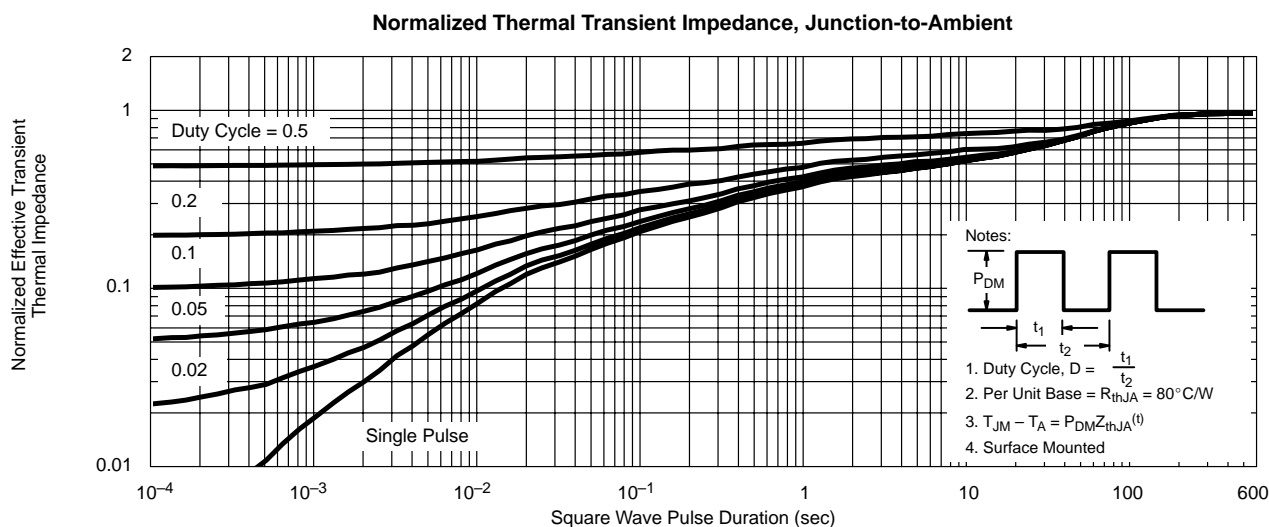
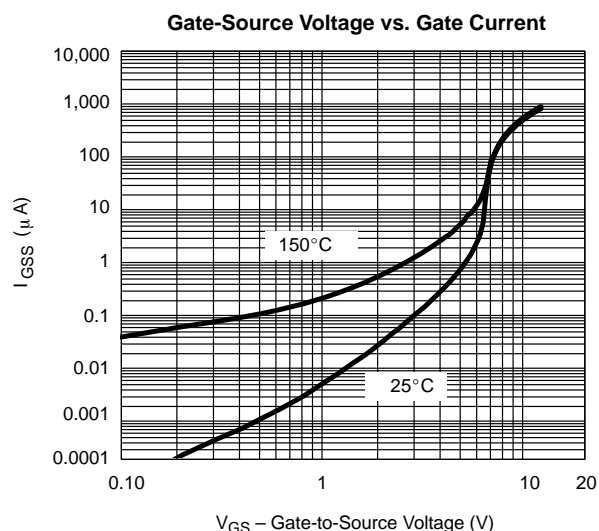
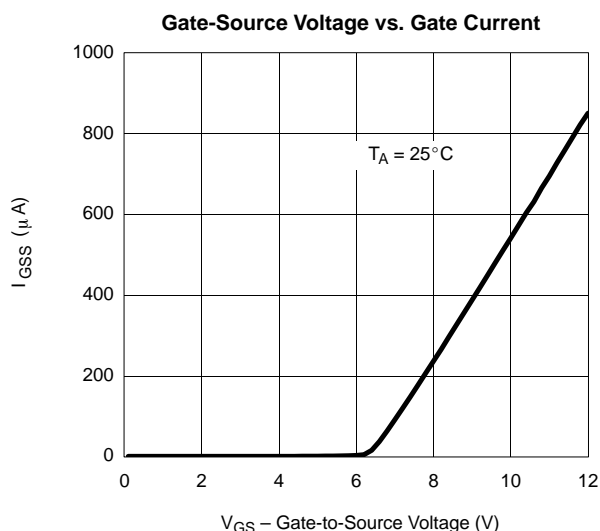
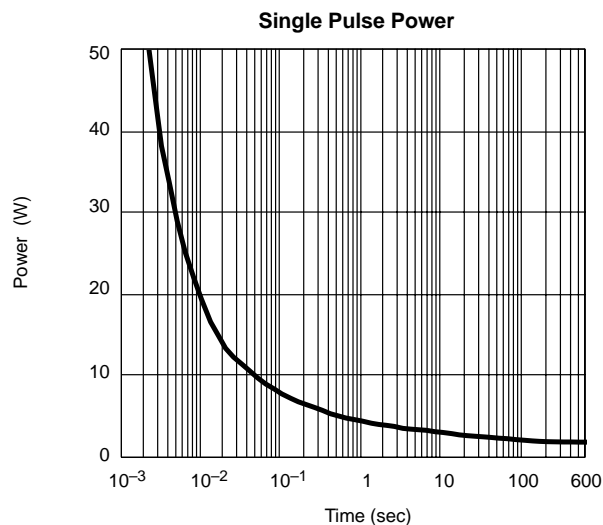
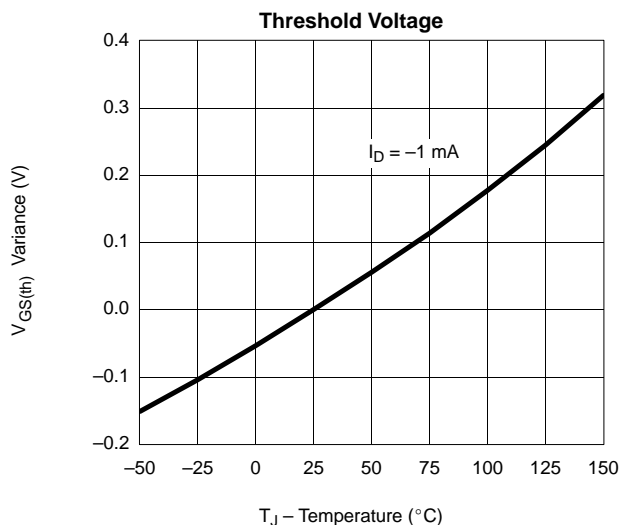
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**





**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

